

Spec. No. : C173E3 Issued Date : 2015.04.10 Revised Date : 2015.08.25

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### 10Amp. Trench Schottky Ultra Low RECTIFIER

# SKT10100E3

IF(AV)	2 x 5A
$V_{RRM}$	100V
VF at 125°C	0.58V
Tj	150°C

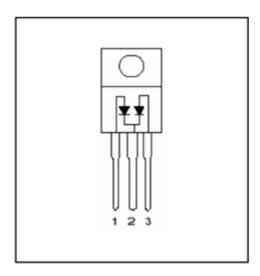
### **Features**

- 150°C operating junction temperature
- Softest, fast switching capability
- High reverse surge capability
- Reduced ultra-low forward voltage drop (VF); better efficiency and cooler operation.
- Lead-Free Finish; RoHS Compliant
- Trench technology provides a superior avalanche capability

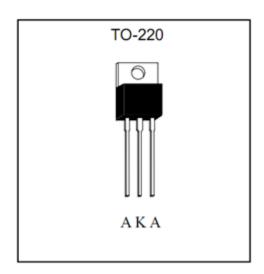
### **Mechanical Data**

- Case: JEDEC TO-220 molded plastic
- Weight: 2.24 grams approximately
- Terminals: Pure tin plated, lead-free, solderable per MIL-STD-750 method 2026
- Epoxy: UL 94V-0 rate flame retardant
- Polarity: As marked.
- Mounting Torque: 5 in-lbs max

### **Equivalent Circuit**



### **Outline**





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### **Maximum Ratings and Electrical Characteristics**

(Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

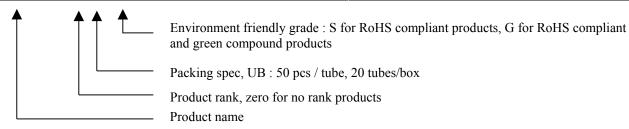
Parameter			Symbol	Min.	Тур.	Max.	Units
Maximum DC blocking voltage			VDC			100	V
Maximum Recurrent peak rever	rse voltage		Vrrm			100	V
Maximum RMS voltage			Vrms			70	V
instantaneous forward voltage a	t Ir—2A nor diada	Tc=25°C	$V_{\mathrm{F}}$		0.39	-	
instantaneous forward voltage at IF=2A per diode Tc=125°C			<b>V</b> F		0.35	-	V
instantaneous forward voltage a	t Ir=5A ner diode	Tc=25°C	$V_{\mathrm{F}}$		0.65	0.72	
instantaneous forward voltage a	t ir—5A per diode	Tc=125°C	<b>V</b> F		0.58	0.66	V
Payarga aurrant par diada	V <sub>R</sub> =100 V, T <sub>C</sub> =25°C V <sub>R</sub> =100 V, T <sub>C</sub> =125°C		Ir		25	80	μΑ
Reverse current per diode					2	12	mA
Maximum Average forward rectified current per device						10	A
Maximum Average forward rectified current per diode			IF(AV)			5	A
Non-repetitive peak forward surge current @			Ifsm				
8.3ms single half sine wave superimposed on				80			Α
rated load (JEDEC method) per diode							
Peak Repetitive Reverse Surge Current (2uS-1Khz)			Irrm			2	A
Storage temperature range			Tstg	-55		150	$^{\circ}\!\mathbb{C}$
Operating junction temperature range			TJ	-55		150	$^{\circ}\!\mathbb{C}$

### **Thermal Data**

Parameter	Symbol	Value	Unit
Typical Thermal Resistance, Junction-to-case	Rth,j-c	2	°C/W
Typical Thermal Resistance, Junction-to-ambient	Rth,j-a	60	°C/W

## **Ordering Information**

Device	Package	Shipping			
SKT10100E3-0-UB-S	TO-220 (Pb-free lead plating)	50 pcs/tube,	20tubes/box,	4boxes/carton	





0

25

50

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## **Typical Characteristics**

Forward Current Derating Curve

6
PER DIODE

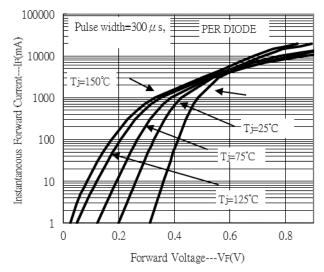
PER DIODE

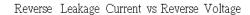
1
resistive or inductive load

75

Case Temperature---TC(℃)

Forward Current vs Forward Voltage

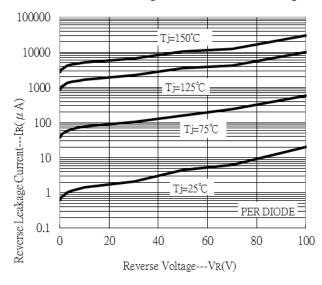




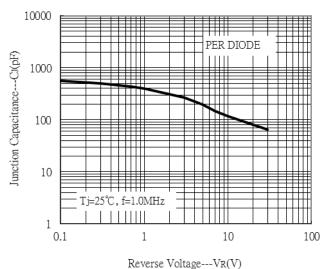
100

125

150



#### Junction Capacitance vs Reverse Voltage





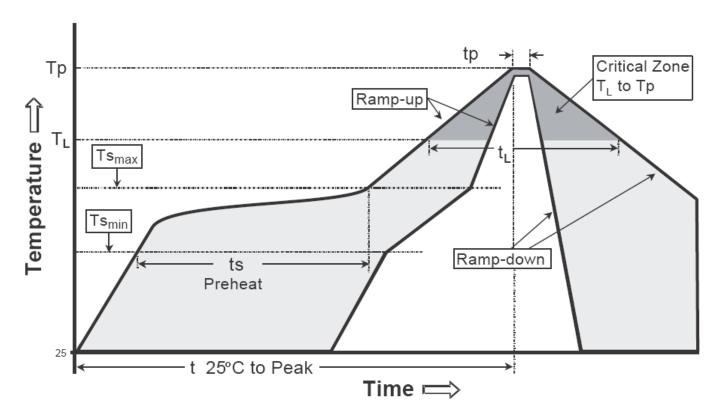
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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

### Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
−Temperature (T∟)	183°C	217°C
– Time (t∟)	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>P</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

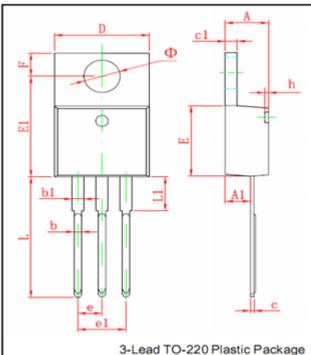
Note: All temperatures refer to topside of the package, measured on the package body surface.



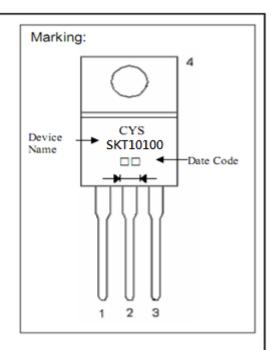
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#### **TO-220 Dimension**



3-Lead TO-220 Plastic Package CYStek Package Code: E3



Style: Pin 1.Anode 2.Cathode 3.Anode

#### \*: Typical

Trypical									
DIM	Millim	eters	Inc	hes	DIM	Millimeters		Inches	
DIIVI	Min. Max. Min. Max.	DIIVI	Min.	Max.	Min.	Max.			
Α	4.470	4.670	0.176	0.184	E1	12.060	12.460	0.475	0.491
A1	2.520	2.820	0.099	0.111	е	2.540*		0.100*	
b	0.710	0.910	0.028	0.036	e1	4.980	5.180	0.196	0.204
b1	1.170	1.370	0.046	0.054	F	2.590	2.890	0.102	0.114
С	0.310	0.530	0.012	0.021	h	0.000	0.300	0.000	0.012
c1	1.170	1.370	0.046	0.054	L	13.400	13.800	0.528	0.543
D	10.010	10.310	0.394	0.406	L1	3.560	3.960	0.140	0.156
E	8.500	8.900	0.335	0.350	Φ	3.735	3.935	0.147	0.155

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material. 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

#### Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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